







SN74HC573A-Q1

ZHCSPX0C - NOVEMBER 2004 - REVISED JUNE 2022

SN74HC573A-Q1 具有三态输出的八路透明 D 型锁存器

1 特性

- 符合汽车应用要求
- 2V 至 6V 的宽工作电压范围
- 高电流三态输出直接驱动总线或多达 15 个 LSTTL 负载
- 低功耗, I_{CC} 最大值为 80 μ A
- t_{pd} 典型值 = 21ns
- 电压为 5V 时,输出驱动为 ±6mA
- 低输出电流,最大值 1µA
- 总线结构引脚分配

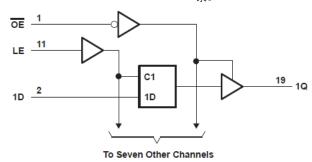
2 说明

该八路透明 D 型锁存器具有专门设计用于驱动高容性 或较低阻抗负载的三态输出。它尤其适用于实现缓冲寄 存器,I/O端口,双向总线驱动器和工作寄存器。

器件信息

	HH		
器件型号	封装 ⁽¹⁾	封装尺寸(标称值)	
SN74HC573AQDW-Q1	SOIC (20)	12.80mm × 7.50mm	
SN74HC573AQPW-Q1	TSSOP (20)	6.50mm × 4.40mm	

(1) 如需了解所有可用封装,请参阅数据表末尾的可订购产品附



功能方框图



Page

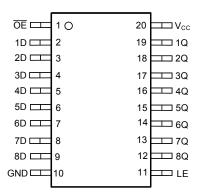
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3 Revision History 注:以前版本的页码可能与当前版本的页码不同		
Changes from Revision B (February 2022) to Revision	on C (June 2022)	Page
Junction-to-ambient thermal resistance values increase	ased. DW was 58 is now 109.1, PW was 83 is no	
Changes from Revision A (April 2008) to Revision B	(February 2022)	Page

• 更新了整个文档中的编号、格式、表格、图和交叉参考,以反映现代数据表标准......1



4 Pin Configuration and Functions



DW or PW Package 20-Pin SOIC or TSSOP Top View



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range		- 0.5	7	V
I _{IK}	Input clamp current ⁽²⁾	$V_I < 0$ or $V_I > V_{CC}$		±20	mA
I _{OK}	Output clamp current ⁽²⁾	$V_O < 0$ or $V_O > V_{CC}$		±20	mA
Io	Continuous output current	$V_O = 0$ to V_{CC}		±35	mA
	Continuous current through V _{CC} or GND		±70	mA	
TJ	Junction temperature			150	$^{\circ}\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!$
T _{stg}	Storage temperature range	- 65	150	$^{\circ}\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!\!$	

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5.2 Recommended Operating Conditions⁽¹⁾

			MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage		2	5	6	V
		V _{CC} = 2 V	1.5			
V_{IH}	High-level input voltage	V _{CC} = 4.5 V	3.15			V
		V _{CC} = 6 V	4.2			
		V _{CC} = 2 V			0.5	
V_{IL}	Low-level input voltage	V _{CC} = 4.5 V			1.35	V
		V _{CC} = 6 V			1.8	
VI	Input voltage	'	0		V _{CC}	V
V _O	Output voltage		0		V _{CC}	V
		V _{CC} = 2 V			1000	
t _t	Input transition (rise and fall) time	V _{CC} = 4.5 V			500	ns
		V _{CC} = 6 V			400	
T _A	Operating free-air temperature	<u>'</u>	-40		125	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

5.3 Thermal Information

		DW (SOIC)	PW (TSSOP)	
THERMAL ME	TRIC	20 PINS	20 PINS	UNIT
R ₀ JA	Junction-to-ambient thermal resistance ⁽¹⁾	109.1	131.8	°C/W
R _{θ JC(top)}	Junction-to-case (top) thermal resistance	76	72.2	°C/W
R ₀ JB	Junction-to-board thermal resistance	77.6	82.8	°C/W
ψJT	Junction-to-top characterization parameter	51.5	21.5	°C/W
ψ ЈВ	Junction-to-board characterization parameter		82.4	°C/W
R _{θ JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report.

Product Folder Links: SN74HC573A-Q1

²⁾ The input and output voltage ratings may be exceeded if the input and output current ratings are observed.



5.4 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CO	EST CONDITIONS V _{CC} T _A = 25°C			T _A = -40°C to 125°C		T _A = -40°C to 85°C		UNIT			
				MIN	TYP	MAX	MIN	MAX	MIN	MAX		
			2 V	1.9	1.998		1.9		1.9			
		I _{OH} = -20 μA	4.5 V	4.4	4.499		4.4		4.4			
V _{OH}	V _I = V _{IH} or V _{IL}		6 V	5.9	5.999		5.9		5.9		V	
		I _{OH} = −6 mA	4.5 V	3.98	4.3		3.7		3.84			
		I _{OH} = -7.8 mA	6 V	5.48	5.8		5.2		5.34			
	V _I = V _{IH} or V _{IL}			2 V		0.002	0.1		0.1		0.1	
		$I_{OL} = 20 \mu A$	4.5 V		0.001	0.1		0.1		0.1		
V _{OL}			6 V		0.001	0.1		0.1		0.1	V	
		I _{OL} = 6 mA	4.5 V		0.17	0.26		0.4		0.33		
		I _{OL} = 7.8 mA	6 V		0.15	0.26		0.4		0.33		
I _I	$V_I = V_{CC}$ or 0		6 V		±0.1	±100		±1000		±1000	nA	
I _{OZ}	$V_O = V_{CC}$ or 0		6 V		±0.01	±0.5		±10		±5	μА	
I _{cc}	$V_I = V_{CC}$ or 0,	I _O = 0	6V			8		160		80	μА	
C _i			2 V to 6 V		3	10		10		10	pF	

5.5 Timing Requirements

over recommended operating free-air temperature range (unless otherwise noted)

		V	T _A = 25°	С	T _A = -40°C t	o 125°C	T _A = -40°C	to 85°C	UNIT
		V _{CC}	MIN	MAX	MIN	MAX	MIN	MAX	UNII
t _w		2 V	80		120		100		
	Pulse duration, LE high	4.5 V	16		24		20		ns
		6 V	14		20		17		
		2 V	50		75		63		
t_{su}	Setup time, data before LE ↓	4.5 V	10		15		13		ns
		6 V	9		13		11		
	Hold time, data after LE ↓	2 V	20		24		24		
t _h		4.5 V	5		5		5		ns
		6 V	5		5		5		



5.6 Switching Characteristics

over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see 🛭 6-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{cc}		= 25°C		T _A = -40°C to 125°C	T _A = -40°C to 85°C	UNIT		
	(IIVF O I)	(0011-01)		MIN	TYP	MAX	MIN MAX	MIN MAX			
			2 V		77	175	265	220			
	D	Q	4.5 V		26	35	53	3 44			
			6 V		23	30	45	38	no		
t _{pd}			2 V		87	175	265	260	ns		
	LE	Any Q	4.5 V		27	35	53	3 44			
					6 V		23	30	45	38	
	en OE	ŌE Any Q	2 V		68	150	225	190			
t _{en}			4.5 V		24	30	45	38	ns		
			6 V		21	26	38	32			
			2 V		47	150	225	190			
t _{dis}	ŌĒ	Any Q	4.5 V		23	30	45	38	ns		
			6 V		21	26	38	32			
			2 V		28	60	90	75			
t _t		Any Q	4.5 V		8	12	18	15	ns		
			6 V		6	10	15	13			

5.7 Switching Characteristics

over recommended operating free-air temperature range, C_L = 150 pF (unless otherwise noted) (see 图 6-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{cc}		= 25°C		T _A = -40°C to 125°C	T _A = -40°C to 85°C	UNIT					
	(01)	(iiti Oi)	(iivi O1)	(1141 01)	(IIVI O1)	(1141 01)	(001101)		MIN	TYP	MAX	MIN MAX	MIN MAX	
			2 V		95	200	300	250						
	D	Q	4.5 V		33	40	60	50						
			6 V		21	34	51	43	ns					
Lpd	t _{pd} LE		2 V		103	225	335	285	115					
		LE	LE	E Any Q	4.5 V		33	45	67	57				
			6 V		29	38	57	48						
			2 V		85	200	300	250						
t _{en}	ŌĒ	Any Q	4.5 V		29	40	60	50	ns					
			6 V		26	34	51	43						
			2 V		60	210	315	265						
t _t		Any Q	4.5 V		17	42	63	53	ns					
			6 V		14	36	53	45						

5.8 Operating Characteristics

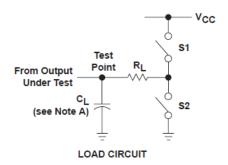
 $T_A = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance per latch	No load	50	pF

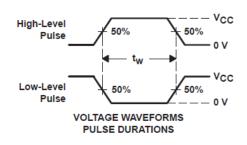
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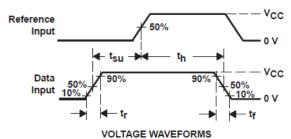
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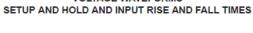
6 Parameter Measurement Information

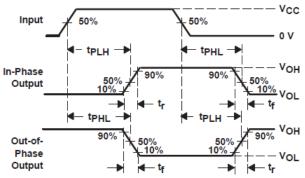


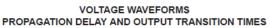
PARAI	PARAMETER		CL	S1	S2
	tPZH 1 kΩ		50 pF	Open	Closed
t _{en}	tpzL	1 K22	or 150 pF	Closed	Open
_	tPHZ			Open	Closed
tdis	t _{PLZ}	t _{PLZ} 1 kΩ 50 pF		Closed	Open
t _{pd} or t _t		1	50 pF or 150 pF	Open	Open

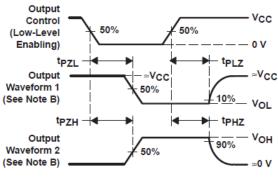












VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES FOR 3-STATE OUTPUTS

- A. C₁ includes probe and test-fixture capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , t_r = 6 ns, t_f = 6 ns.
- D. The outputs are measured one at a time, with one input transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .

图 6-1. Load Circuit and Voltage Waveforms

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7 Detailed Description

7.1 Overview

This octal transparent D-type latch features 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. It is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

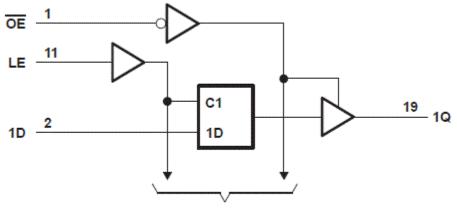
While the latch-enable (LE) input is high, the Q outputs respond to the data (D) inputs. When LE is low, the outputs are latched to retain the data that was set up.

A buffered output-enable (\overline{OE}) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to VCC through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

 $\overline{\text{OE}}$ does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

7.2 Functional Block Diagram



To Seven Other Channels

7.3 Device Functional Modes

表 7-1. Function Table (Each Latch)

	OUTPUT		
ŌĒ	LE	Q	
L	Н	Н	Н
L	Н	L	L
L	L	Х	Q ₀
Н	Х	X	Z

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8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

9 Layout

9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.



10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 接收文档更新通知

要接收文档更新通知,请导航至 ti.com 上的器件产品文件夹。点击*订阅更新* 进行注册,即可每周接收产品信息更改摘要。有关更改的详细信息,请查看任何已修订文档中包含的修订历史记录。

10.2 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料,可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者"按原样"提供。这些内容并不构成 TI 技术规范,并且不一定反映 TI 的观点;请参阅 TI 的《使用条款》。

10.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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10.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.5 术语表

TI术语表本术语表列出并解释了术语、首字母缩略词和定义。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74HC573AQDWRQ1	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HC573AQ	Samples
SN74HC573AQPWRG4Q1	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HC573AQ	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

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PACKAGE OPTION ADDENDUM

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OTHER QUALIFIED VERSIONS OF SN74HC573A-Q1:

● Catalog : SN74HC573A

• Military : SN54HC573A

NOTE: Qualified Version Definitions:

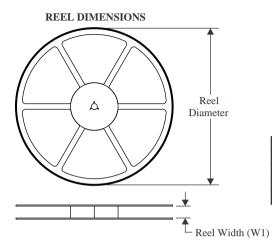
• Catalog - TI's standard catalog product

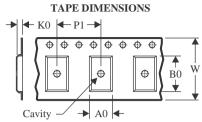
• Military - QML certified for Military and Defense Applications

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HC573AQDWRQ1	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN74HC573AQPWRG4Q1	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74HC573AQPWRG4Q1	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
SN74HC573AQDWRQ1	SOIC	DW	20	2000	367.0	367.0	45.0	
SN74HC573AQPWRG4Q1	TSSOP	PW	20	2000	356.0	356.0	35.0	
SN74HC573AQPWRG4Q1	TSSOP	PW	20	2000	356.0	356.0	35.0	



SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



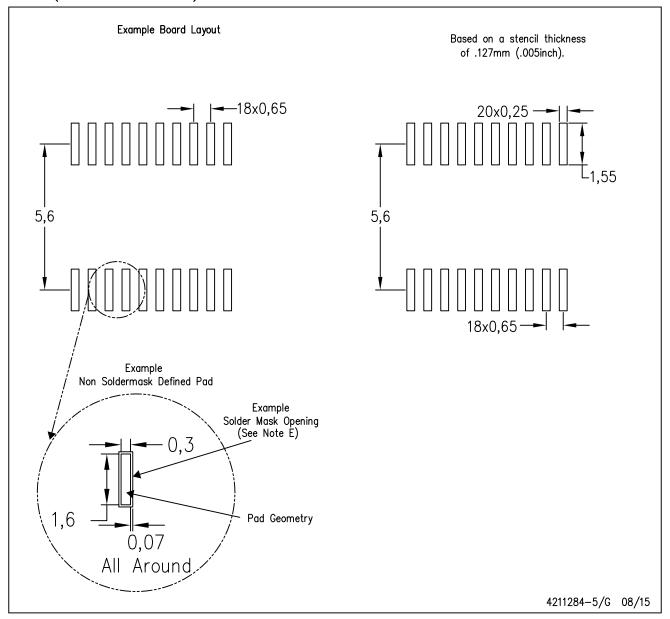
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



NOTES:

- All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





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NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



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NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



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NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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